

ABSTRACT OF THE DISCLOSURE

An interlayer dielectric film is formed to cover a gate electrode part formed on the surface of a semiconductor substrate. A shared contact hole exposing both of the upper surface of the gate electrode part and the
5 surface of a cobalt silicide film is formed in the interlayer dielectric film. A side wall nitride film is formed on the side surface of the shared contact hole. On the surface of a lower portion of a side wall insulator film located on the bottom of the shared contact hole, a side wall nitride film is formed
10 to cover the surface of a portion of a region of the semiconductor substrate located under the side wall insulator film. A barrier metal layer and a plug are formed in the shared contact hole. Thus, a semiconductor device suppressing a leakage current is obtained.